



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic Part Number	IPD082N10N3G
▶ Overseas Part Number	IPD082N10N3G
▶ Equivalent Part Number	IPD082N10N3G

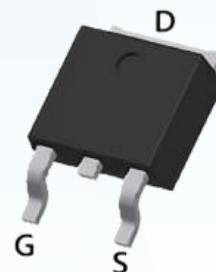


V _{DSS} (V)	R _{DS} (ON)	I _D (A)
100	8.5mΩ(Typ)@VGS=10V	70
	9.5mΩ(Typ)@VGS=4.5V	

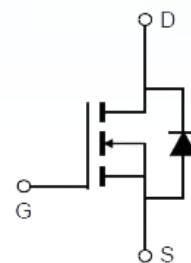
FEATURE:

- The IPD082N10N3G is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Pin Description

TO-252

**Absolute Maximum Ratings**

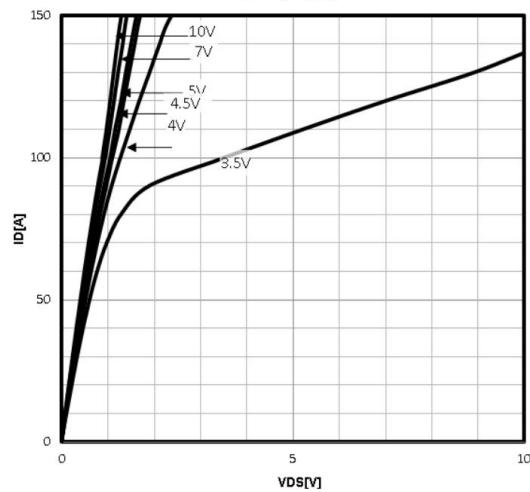
Symbol	Parameter	Rating	Units
V _{DSS}	Drain-Source Voltage	100	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current(V _{GS} = -4.5V)	T _c =25°C	70
		T _c =70°C	45
T _J	Maximum Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
I _{DM}	Pulsed Drain Current	280	A
P _D	Maximum Power Dissipation	T _c =25°C	100
		T _c =70°C	---
E _{AS}	Avalanche Energy, Single Pulsed	110	mJ
R _{θJC}	Thermal Resistance-Junction to Case	1.25	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient	64	°C/W

Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

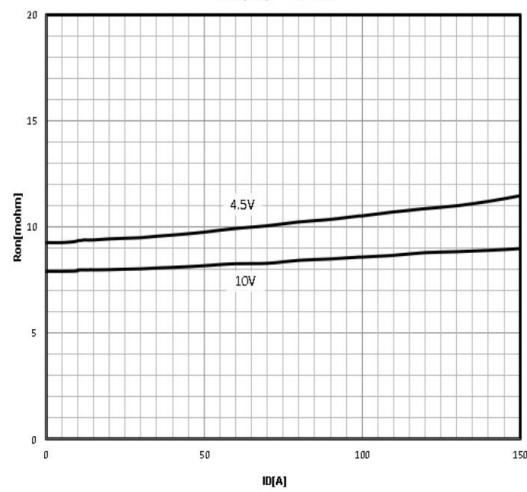
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250uA	100	---	---	V
VGS(th)	Gate threshold voltage	VDS=VGS, ID=250uA	1.2	1.8	2.5	V
RDS(on)	Drain-Source On-state Resistance	VGS=10V , ID=20A	---	8.5	10.5	mΩ
		VGS=4.5V , ID=15A	---	9.5	15	mΩ
IGSS	Gate-source leakage current	VGS=±20V , VDS=0V	---	---	±100	nA
IDSS	Zero gate voltage drain current	VDS=100V, VGS=0V, TJ=25°C	---	---	1	μA
		TJ=55°C	---	---	---	
Dynamic Characteristic						
Ciss	Input Capacitance	VGS=0V, VDS=50V, Frequency=1.0MHz	---	1368	---	pF
Coss	Output Capacitance		---	451	---	
Crss	Reverse Transfer Capacitance		---	12.9	---	
QG	Gate Total Charge	VDS=50V, VGS=10V, IDS=10A	---	31.3	---	nC
Qgs	Gate-Source charge		---	3.49	---	
Qgd	Gate-Drain charge		---	7.63	---	
td(on)	Turn-on delay time	VDD=50V , VGS=10V , RG=4Ω, ID=10A	---	16	---	ns
tr	Turn-on Rise Time		---	10	---	
td(off)	Turn-off Delay Time		---	40	---	
tf	Turn-off Fall Time		---	6	---	
RG	Gate Resistance	VGS=0V,VDS=0V,F=1MHz	---	0.48	---	Ω
Diode Characteristics						
Is	Diode Forward Current		--	--	70	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		---	--	---	A
VSD	Diode Forward Voltage	VGS=0V , IS=1A , TJ=25°C	---	---	1.2	V
trr	Reverse Recovery Time	ISD=4.1A, dISD/dt=-100A/μs	---	103	---	ns
Qrr	Reverse Recovery Charge		---	187	---	nC

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

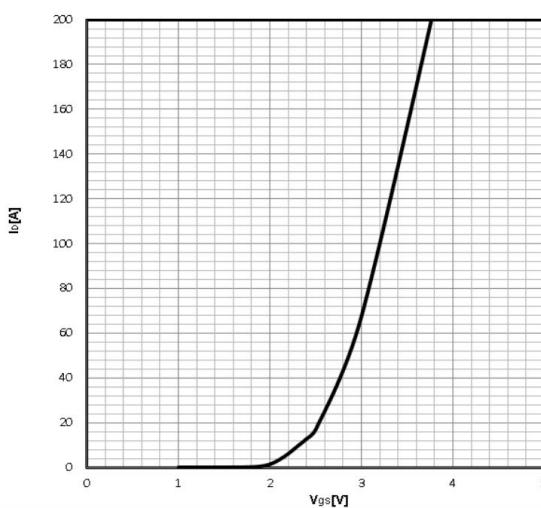
Typ. output characteristics
 $I_D=f(V_{DS})$



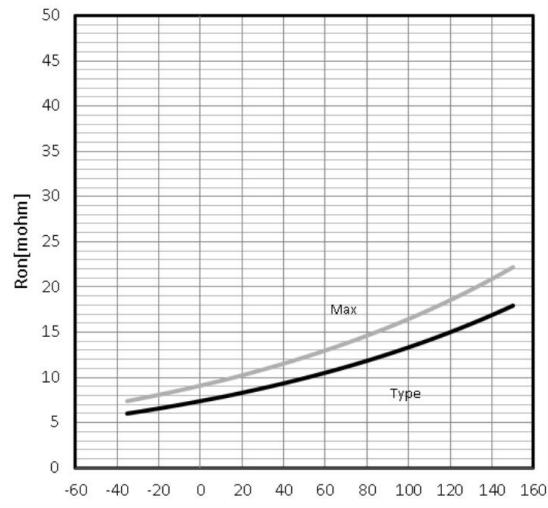
Typ. drain-source on resistance
 $R_{DS(on)}=f(I_D)$



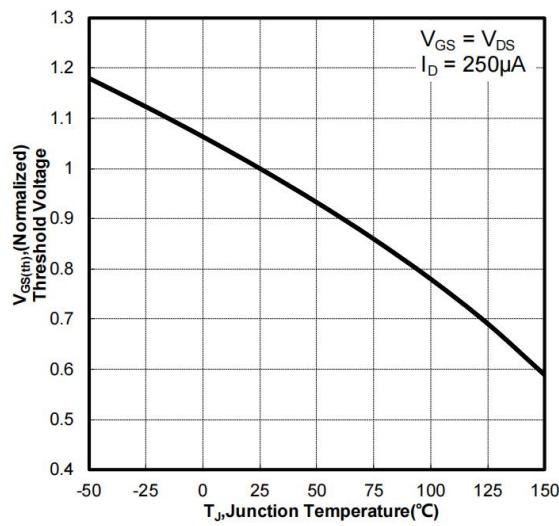
Typ. transfer characteristics
 $I_D=f(V_{GS})$



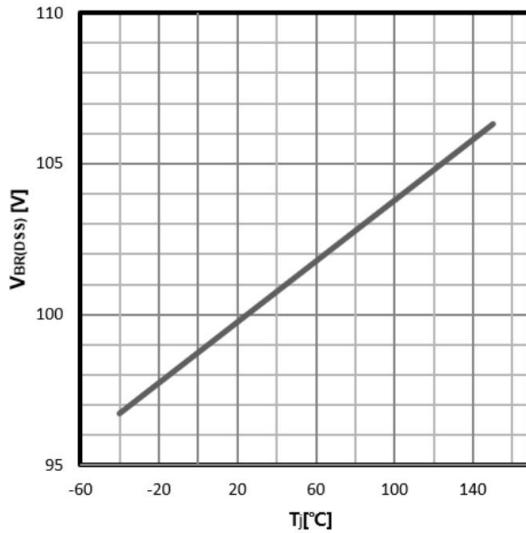
Drain-source on-state resistance
 $R_{DS(on)}=f(T_j); I_D=20A; V_{GS}=10V$



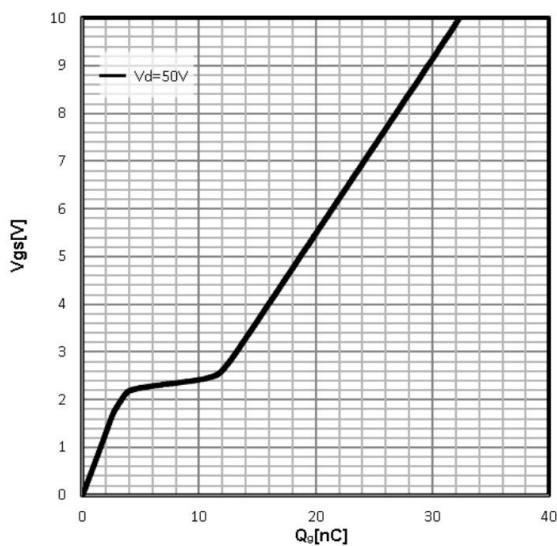
Gate Threshold Voltage
 $V_{TH}=f(T_j)$; $I_D=250\mu A$



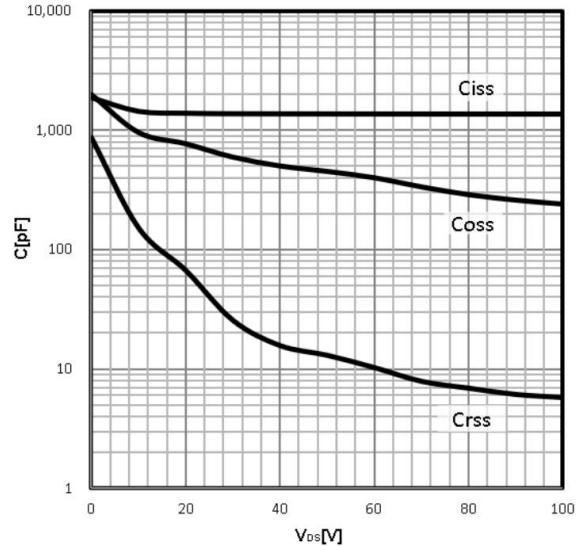
Drain-source breakdown voltage
 $V_{BR(DSS)}=f(T_j)$; $I_D=250\mu A$

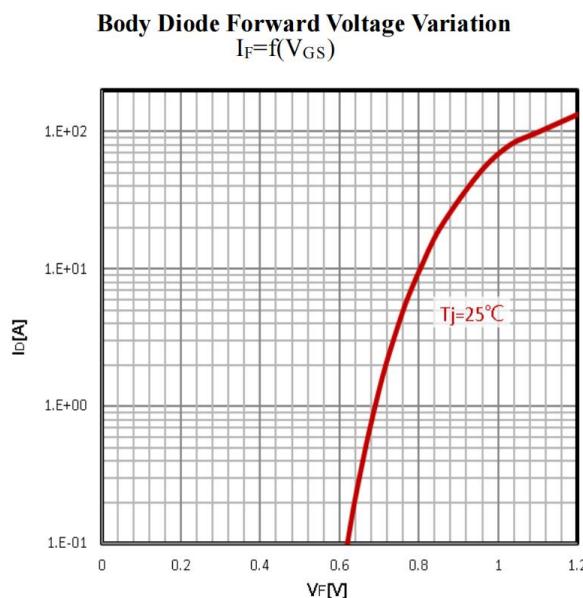
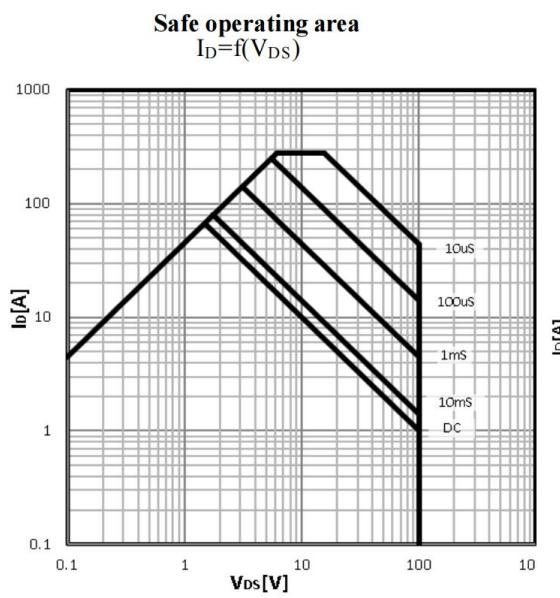
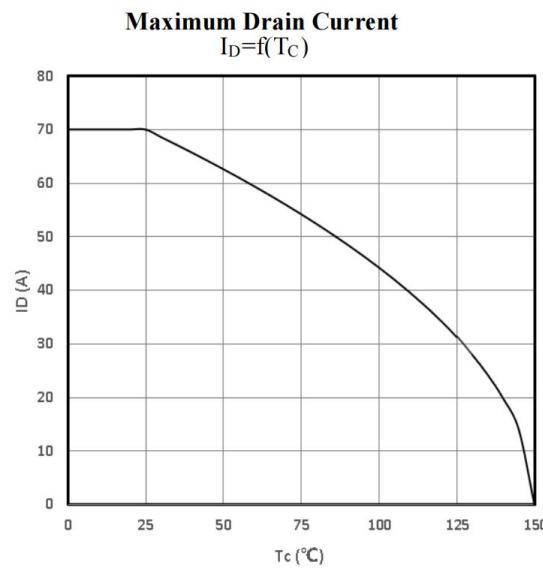
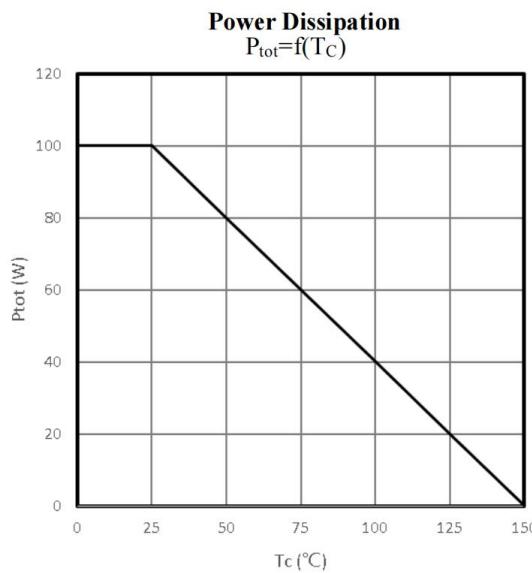


Typ. gate charge
 $V_{GS}=f(Q_g)$; $I_D=10A$



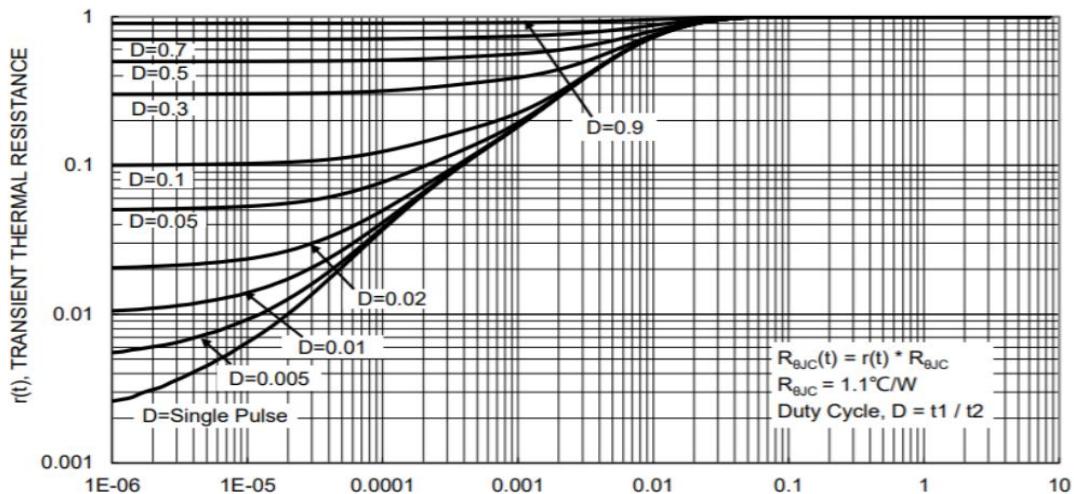
Typ. capacitances
 $C=f(V_{DS})$; $V_{GS}=0V$; $f=1MHz$

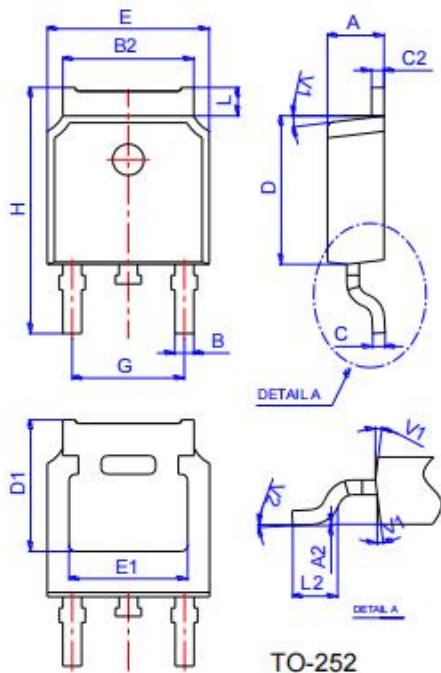




Max. transient thermal impedance

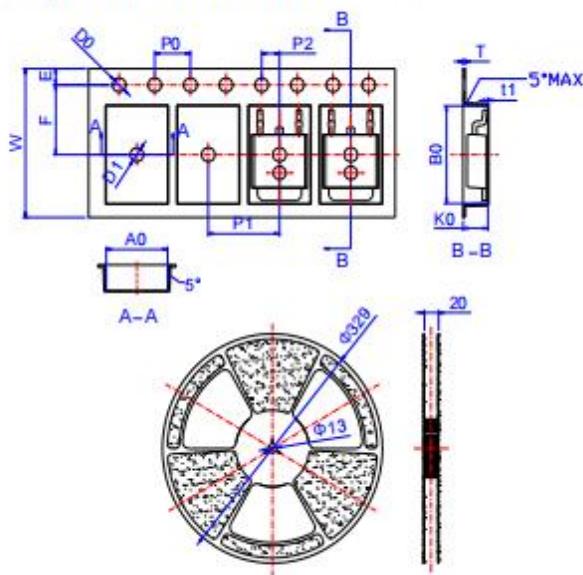
$$Z_{thJC} = f(t_p)$$



Package Mechanical Data:TO-252-3L


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1	7°			7°		
V2	0°		6°	0°		6°

TO-252

Reel Specification-TO-252


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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